## UNITED STATES PATENT AND TRADEMARK OFFICE

## **CERTIFICATE OF CORRECTION**

PATENT NO.

: 7,169,632 B2

Page 1 of 2

APPLICATION NO.: 10/657841

DATED

: January 30, 2007

INVENTOR(S)

: Johannes Baur et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Page 2, column 1, line 8,

Item [56] U.S. PATENT DOCUMENTS,

insert 6,291,839 B1	09/2001	Lester
3,343,026	09/1967	Luechinger et al.
5,814,839	09/1998	Hosoba
5,087,674	02/1992	Gardner et al.
2003/0116791 A1	06/2003	Baptist et al.
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Page 2, column 2, line 7,

Item [56] FOREIGN PATENT DOCUMENTS,

insert	DE	199 27 945 A1	03/2000
	DE	198 07 758 A1	12/1998
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	DE	42 18 806 A1	12/1993
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	WO	01/61765 A1	08/2001
	UK	2 271 087 A	04/1994
	EP	0 611 131 A1	08/1994
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	EP	0 442 002 A1	08/1991
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Page 2, column 2, line 7,

Item [56] OTHER PUBLICATIONS

insert -- J. Zhang et al. "Precise microfabrication of wide band gap semiconductors (SiC and GaN) by VUV-UV multiwavelength laser ablation", Applied Surface Science, Vol. 127-129, pp. 793-799, 1998.

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Page 2, column 2, line 7,

Item [56] OTHER PUBLICATIONS (cont'd)

W. N. Carr. "Photometric Figures of Merit for Semiconductor Luminescent Sources Operating in Spontaneous Mode", Infrared Physics, Vol. 6, pp. 1-19, 1966. --

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Signed and Sealed this

Twelfth Day of June, 2007

JON W. DUDAS
Director of the United States Patent and Trademark Office